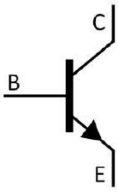
SOT-23　　NPN　　Silicon NPN transistor in a SOT-23 Plastic Package.

V_{CEO}

High Collector-Emitter Voltage.

High voltage application.



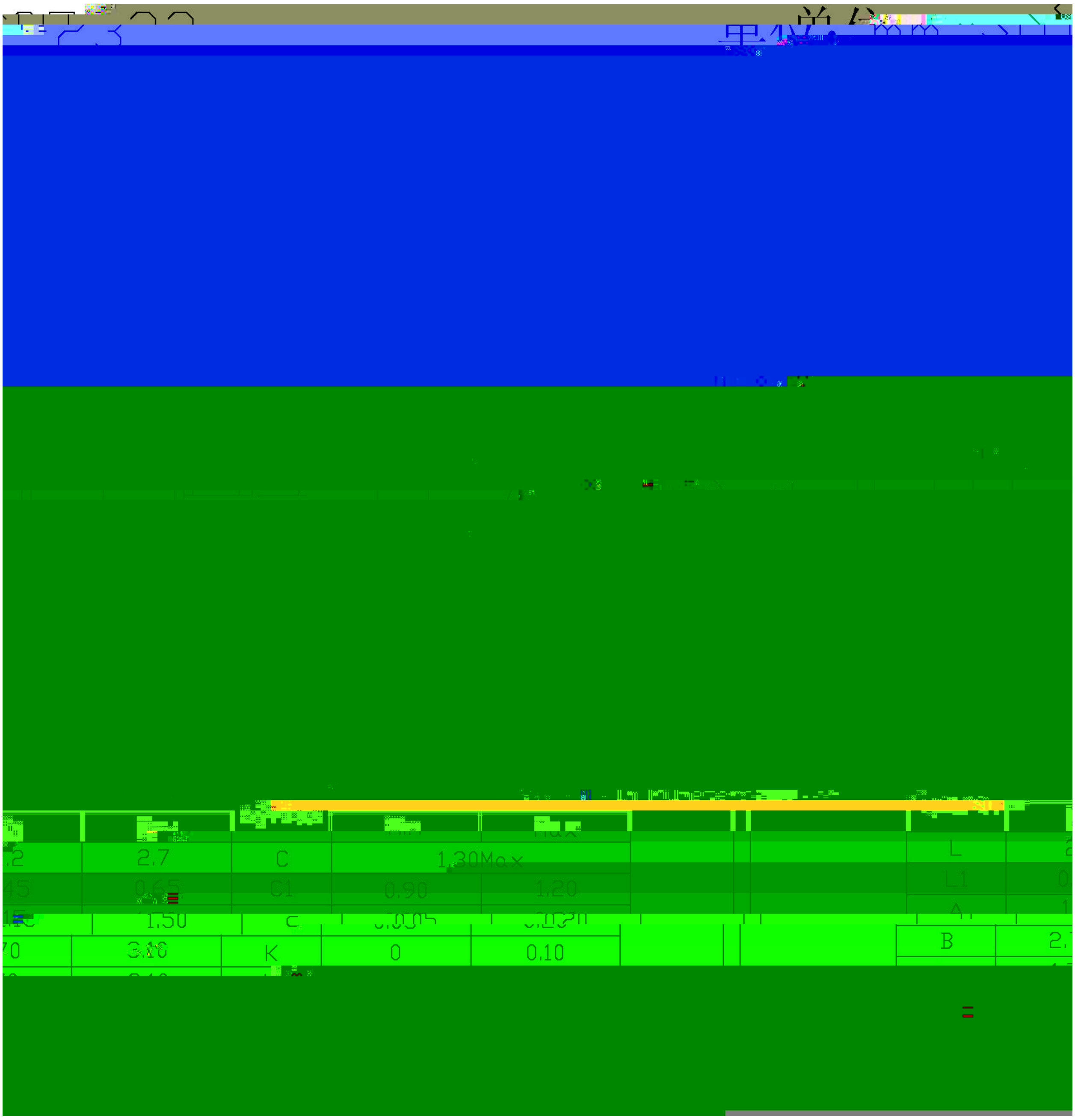
PIN1　Base　　PIN 2　Emitter　　PIN 3　Collector

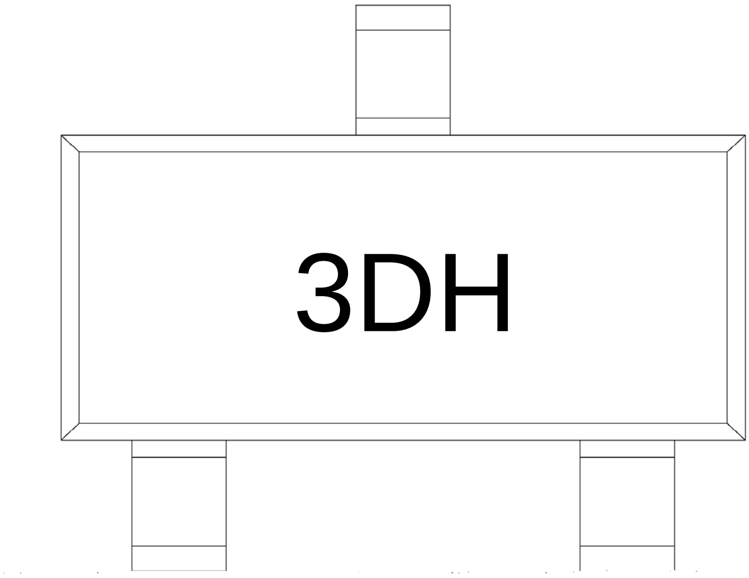
h_{FE} Range	30~200
Marking	3DH

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	350	V
Collector to Emitter Voltage	V_{CEO}	350	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	500	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55˙ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit

Collector to Base Breakdown
V


2.7
C
1.30Max
0.65
C1
0.90
1.20
1.50
0.10
K
0
L
L1
A
B



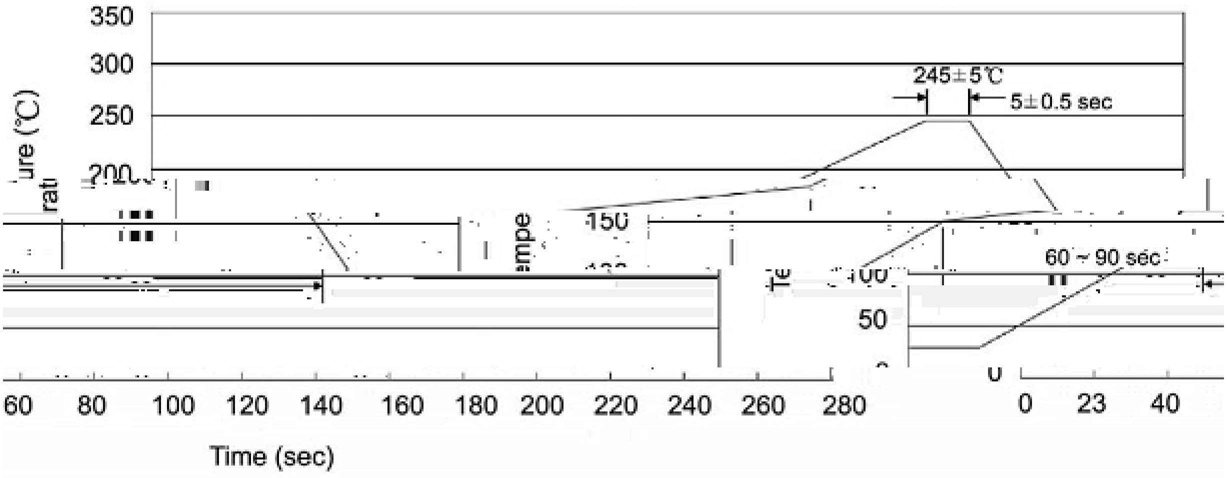
3D

H

Note:

3D	Product Type Code
H	Company Code

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1 25 150 60 90sec; 1.Preheating:25~150 , Time:60~90sec.

2 245±5 5±0.5sec; 2.Peak Temp.:245±5 , Duration:5±0.5sec.

3 2 10 /sec. 3. Cooling Speed: 2~10 /sec.

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type	Units					Dimension	(unit mm^3)	
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7 ρ ×8	180×120×180	390×385×205